

Vishay Siliconix

RoHS

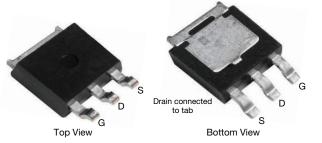
COMPLIANT HALOGEN

FREE

Automotive N-Channel 100 V (D-S) 175 °C MOSFET

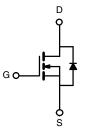
PRODUCT SUMMARY				
V _{DS} (V)	100			
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.025			
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.029			
I _D (A)	40			
Configuration	Single			
Package	TO-252 Reverse Lead DPAK			





FEATURES

- TrenchFET[®] power MOSFET
- Package with low thermal resistance
- 100 % $R_{\rm q}$ and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C =$	25 °C, unles	s otherwise noted)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	100	V
Gate-Source Voltage		V _{GS}	± 20	v
Continuous Drain Current	$T_C = 25 ^{\circ}C^a$	I-	40	
Continuous Drain Current	$T_C = 125 \ ^\circ C$	I _D	26	
Continuous Source Current (Diode Conduction) a		I _S	40	А
Pulsed Drain Current ^b		I _{DM}	160	
Single Pulse Avalanche Current L = 0.1 mH		I _{AS}	40	
Single Pulse Avalanche Energy	L = 0.1 mm	E _{AS}	80	mJ
Maximum Power Dissipation ^b	T _C = 25 °C	PD	136	w
	$T_C = 125 \ ^\circ C$	۳D	45	٧V
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	50	°C/W	
Junction-to-Case (Drain)		R _{thJC}	1.1	C/W	

Notes

a. Package limited.

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

c. When mounted on 1" square PCB (FR4 material).

1



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		100	-	-	v
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μΑ	1.5	-	2.5	v
Gate-Source Leakage	I _{GSS}	V _{DS} =	: 0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 100 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 100 V, T _J = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	V _{DS} = 100 V, T _J = 175 °C	-	-	250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α
Drain-Source On-State Resistance ^a		$V_{GS} = 10 V$	I _D = 40 A	-	0.019	0.025	
		V _{GS} = 10 V	I _D = 40 A, T _J = 125 °C	-	-	0.050	
	R _{DS(on)}	V _{GS} = 10 V	I _D = 40 A, T _J = 175 °C	-	-	0.063	Ω
		$V_{GS} = 4.5 V$	I _D = 20 A	-	0.021	0.029	
Forward Transconductance ^b	g fs	V _{DS}	= 15 V, I _D = 40 A	-	73	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	2703	3380	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	312	390	pF
Reverse Transfer Capacitance	C _{rss}			-	127	160	
Total Gate Charge ^c	Qg			-	46	70	
Gate-Source Charge ^c	Q _{gs}	$V_{GS} = 10 V$	$V_{DS} = 50 \text{ V}, I_D = 40 \text{ A}$	-	8.2	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	13	-	
Gate Resistance	Rg	f = 1 MHz		0.9	1.8	3.1	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	11	17	
Rise Time ^c	t _r	$\label{eq:VDD} \begin{array}{l} V_{DD}=50 \text{ V}, \ R_L=1.25 \ \Omega \\ I_D\cong 40 \text{ A}, \ V_{GEN}=10 \text{ V}, \ R_g=1 \ \Omega \end{array}$		-	11	17	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	27	41	
Fall Time ^c	t _f			-	6	9	
Source-Drain Diode Ratings and Chara	acteristics ^b	•					
Pulsed Current ^a	I _{SM}			-	-	160	Α
		$I_{\rm F} = 40$ A, $V_{\rm GS} = 0$ V					

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

T_C =

T_C = 25 °C

36

48

60

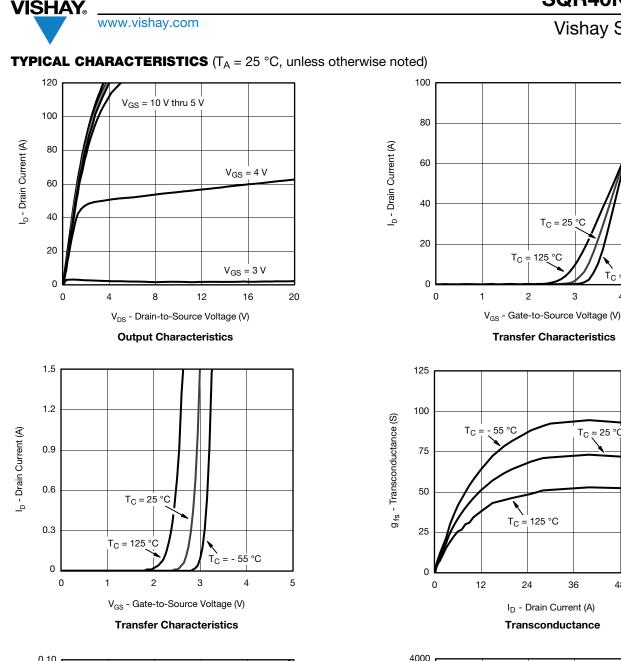
4

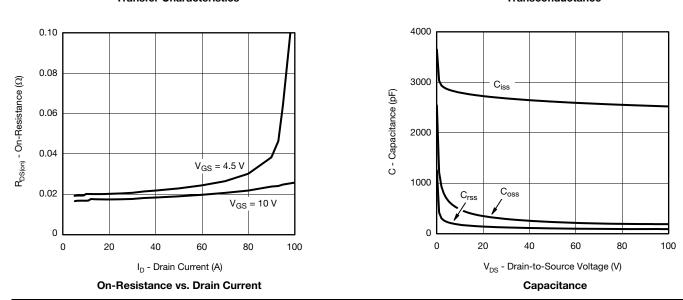
3

- 55 °C

5

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S15-1873-Rev. F, 10-Aug-15

3

Document Number: 69060

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 $I_D = 40 \text{ Å}$ 2.1 $V_{DS} = 50 V$

2.5



V_{GS} = 10 V

125

T_J = 150 °C

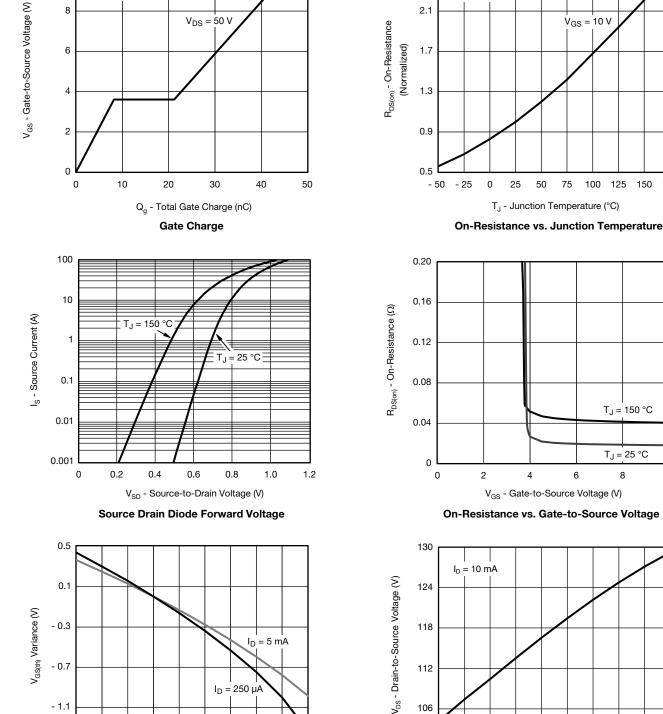
T_J = 25 °C

8

10

150 175

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I_D = 250 μA

T_J - Temperature (°C) **Threshold Voltage**

125 150 175

TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

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10

8

 $I_D = 40$ A

S15-1873-Rev. F, 10-Aug-15

- 50 - 25

0 25 50 75 100

- 1.1

- 1.5

4

106

100

- 50

- 25 0 50

75

T_{.1} - Junction Temperature (°C)

Drain Source Breakdown vs. Junction Temperature

25

Document Number: 69060

175

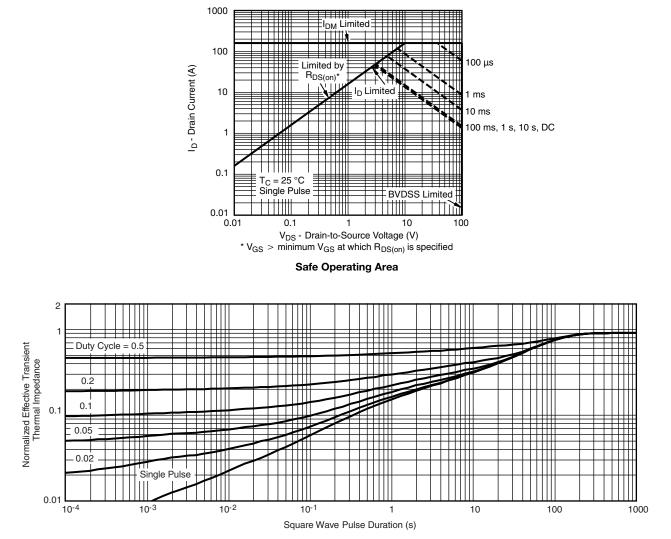
100 125 150

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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



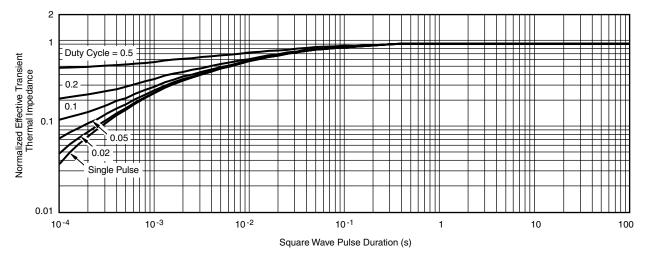
Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

S15-1873-Rev. F, 10-Aug-15

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?69060.



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REVISION	HISTORY ^a	
REVISION	DATE	DESCRIPTION OF CHANGE
F	04-Aug-15	Revised R _g minimum limit

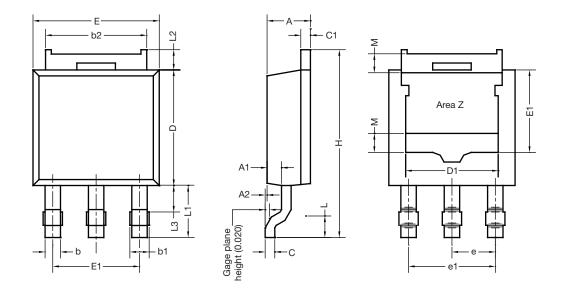
Note

a. As of April 2014



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TO-252 Reverse Lead Case Outline



Notes

Dimension L3 for reference only

• Area Z: unplated area more than 80 % heatsink area and for partial plating part only

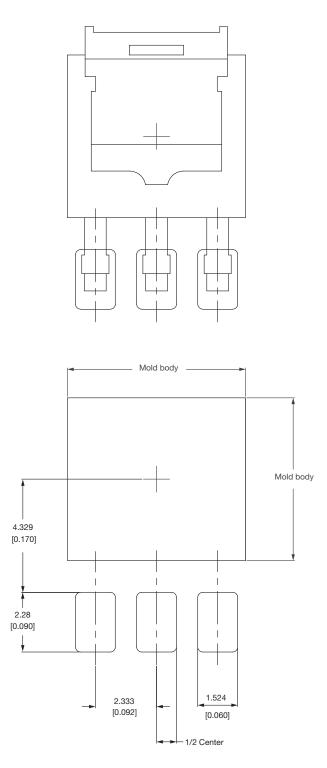
DIM.	MIL	LIMETERS	INCHES		
	MIN.	MAX.	MIN.	MAX.	
А	2.23	2.33	0.088	0.092	
A1	0.64	0.89	0.025	0.035	
A2	0.03	0.18	0.001	0.007	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.49	5.00	0.177	0.197	
E	6.48	6.73	0.255	0.265	
E1	4.32	-	0.170	-	
е	2.28 BSC		0.090 BSC		
e1	4.57 BSC		0.180 BSC		
Н	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	2.74 BSC		(0.108 BSC	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
М	-	1.00 (reference only)	-	0.039 (reference only	



PAD Pattern

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Recommended Land Pattern DPAK (TO-252) 3LR



Note

• Dimensions in mm (inches)

ECN: T22-0575-Rev. A, 12-Dec-2022 DWG: 3015

Revision: 12-Dec-2022

1

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